

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1339	438/149.ccls. or 438/151.ccls.	USPAT	OR	ON	2005/08/02 17:02
L2	47	1 and ((first adj mask) and (second adj mask) and (third adj mask))	USPAT	OR	ON	2005/08/02 17:08
L3	3388	438/149-166.ccls.	USPAT	OR	ON	2005/08/02 17:08
L4	2993	3 and (source and drain)	USPAT	OR	ON	2005/08/02 17:08
L5	274	4 and (mask and dielectric and passivation and silicon)	USPAT	OR	ON	2005/08/02 17:08
L6	217	5 and (amorphous adj silicon)	USPAT	OR	ON	2005/08/02 17:08
L7	21	6 and ((first adj mask) and (second adj mask) and (third adj mask))	USPAT	OR	ON	2005/08/02 17:09
L8	17554	(source and drain and gate and dielectric and (thin adj film) or TFT)	US-PGPUB	OR	ON	2005/08/02 17:17
L9	6061	8 and (amorphous near silicon)	US-PGPUB	OR	ON	2005/08/02 17:17
L10	6124	8 and (amorphous near2 silicon)	US-PGPUB	OR	ON	2005/08/02 17:11
L11	6058	8 and (amorphous adj silicon)	US-PGPUB	OR	ON	2005/08/02 17:18
L12	307	11 and ((first and second and third and fourth) adj mask)	US-PGPUB	OR	ON	2005/08/02 17:18
L13	198	12 and (etch\$3 and passivation)	US-PGPUB	OR	ON	2005/08/02 17:14
L14	142	12 and (etch\$3 with passivation)	US-PGPUB	OR	ON	2005/08/02 17:18
L16	82644	(source and drain and gate and dielectric and (thin adj film) or TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 17:17
L18	15340	16 and (amorphous adj silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 17:18
L19	502	18 and ((first and second and third and fourth) adj mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 17:18
L20	232	19 and (etch\$3 with passivation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 17:19

L21	178	20 and (transparent with conduct\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 17:19
S1	0	"438"/\$.ccls. and tft.in.	USPAT	OR	ON	2005/03/16 19:15
S2	121	"438"/\$.ccls. and tft.ti.	USPAT	OR	ON	2005/03/16 19:18
S3	1260	438/149.ccls. or 438/151.ccls.	USPAT	OR	ON	2005/08/02 17:02
S4	3252	438/149-166.ccls.	USPAT	OR	ON	2005/08/02 17:08
S5	2870	S4 and (source and drain)	USPAT	OR	ON	2005/08/02 17:08
S6	258	S5 and (mask and dielectric and passivation and silicon)	USPAT	OR	ON	2005/08/02 17:08
S7	216	S6 and (gate adj electrode)	USPAT	OR	ON	2005/03/16 19:20
S8	177	S7 and (amorphous adj silicon)	USPAT	OR	ON	2005/08/02 17:08
S9	17	S8 and ((first adj mask) and (second adj mask) and (third adj mask))	USPAT	OR	ON	2005/08/02 17:08
S10	2	S7 and ((amorphous adj silicon) with seed)	USPAT	OR	ON	2005/03/16 19:24
S11	82	S4 and ((amorphous adj silicon) with seed)	USPAT	OR	ON	2005/03/16 19:24
S12	9	S4 and ((amorphous adj silicon) with (seed adj layer))	USPAT	OR	ON	2005/03/16 19:25